

ABSTRACT

A low-k dielectric layer (104) is treated with a dry-wet (D-W) or dry-wet-dry (D-W-D) process to improve patterning. Resist poisoning occurs due to an interaction between low-k films (104), such as OSG, and DUV resist (130). The D-W or D-W-D treatment is performed to either pretreat a low-k dielectric (104) before forming the pattern (130) or during a rework of the pattern (130).

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